In the Claims:

1. (Currently amended) A polishing composition suitable for polishing semiconductor substrates having a non-ferrous interconnect comprising:

0.1 to 1.5 wt% of a polyvinyl alcohol~~thermoplastic polymer~~; ~~and~~

0.01 to 0.85 wt% of polyvinylpyrrolidone;

up to 10 wt% of a corrosion inhibitor;

up to 15 wt% complexing agent;

up to 10 wt% of an oxidizing agent; and

0.05 to 40 wt% of an abrasive wherein the polishing composition has a pH of at least 7 and wherein ~~varying~~ increasing the weight ratio of the ~~thermoplastic polymer~~polyvinyl alcohol to the polyvinylpyrrolidone ~~controls~~ decreases the removal rate of the non-ferrous interconnect.

2. (Currently amended) The composition of Claim 1, wherein the polyvinylpyrrolidone has a weight average molecular weight of 1,000 to 250,000 g/mole. ~~thermoplastic polymers are polyacetals, polyacrylics, polycarbonates polystyrenes, polyesters, polyamides, polyamideimides, polyarylates, polyarylsulfones, polyethersulfones, polyphenylene sulfides, polysulfones, polyimides, polyetherimides, polytetrafluoroethylenes, polyetherketones, polyether etherketones, polyether ketone ketones, polybenzoxazoles, polyoxadiazoles, polybenzothiazinophenothiazines, polybenzothiazoles, polypyrazinoquinoxalines, polypyromellitimides, polyquinoxalines, polybenzimidazoles, polyoxindoles, polyoxoisoindolines, polydioxoisoindolines, polytriazines, polypyridazines, polypiperazines, polypyridines, polypiperidines, polytriazoles, polypyrazoles, polycarboranes, polyoxabicyclononanes, polydibenzofurans, polyphthalides, polyacetals, polyanhydrides, polyvinyl ethers, polyvinyl thioethers, polyvinyl alcohols, polyvinyl ketones, polyvinyl halides, polyvinyl nitriles, polyvinyl esters, polysulfonates, polysulfides, polythioesters, polysulfones, polysulfonamides, polyureas, polyphosphazenes, polysilazanes, or a combination comprising at least one of the foregoing thermoplastic polymers~~.

3. (Currently amended) The composition of Claim 1, ~~further comprising 0.1 to 40 wt% of~~wherein the abrasive particles include silica particles.

4. (Currently amended) The composition of Claim 1, wherein the ~~thermoplastic polymer is a polyvinylalcohol having~~ polyvinyl alcohol has a weight average molecular weight of 1,000 to 1,000,000 grams per mole and a degree of hydrolyzation of at least 20 mole percent, wherein the mole percent is based upon the total number of moles of the polyvinylalcohol.

5. (Original) The composition of Claim 1, wherein the polyvinylpyrrolidone has a weight average molecular weight of 100 to 1,000,000 grams per mole.

6. (Original) The composition of Claim 1, wherein the polyvinylpyrrolidone and the thermoplastic polymer is present in the polishing composition in a weight ratio of 1:10 to 100:1 respectively.

7. (Previously presented) A polishing composition suitable for polishing semiconductor substrates having a nonferrous interconnect comprising:

0.1 to 1.5 wt% of polyvinyl alcohol having a weight average molecular weight of ~~13,000~~3,000 to ~~23,000~~500,000 g/mole;

0.01 to 0.85 wt% of polyvinylpyrrolidone having a weight average molecular weight of ~~3,000~~1,000 to ~~10,000~~250,000 g/mole;

up to 10 wt% of a corrosion inhibitor;

up to 15 wt% complexing agent;

up to 10 wt% of an oxidizing agent; and

0.1 to 40 wt% of a silica abrasive; wherein the polishing composition has a pH of at least 7, and further wherein ~~varying~~ increasing the weight ratio of the ~~thermoplastic polymer~~polyvinyl alcohol to the polyvinylpyrrolidone ~~controls~~ decreases the removal rate of the non-ferrous interconnect.

8. (Currently amended) A method of polishing a semiconductor substrate having a non-ferrous interconnect comprising the steps of:

applying a polishing composition comprising 0.1 to 1.5 wt% of a polyvinyl alcohol; 0.01 to 0.85 wt% of polyvinylpyrrolidone; up to 10 wt% of a corrosion inhibitor;

up to 15 wt% complexing agent; up to 10 wt% of an oxidizing agent; and 0.1 to 40 wt% of an abrasive wherein the polishing composition has a pH of at least 7~~0.1 to 1.5 wt% of a thermoplastic polymer; and 0.01 to 0.85 wt% of polyvinylpyrrolidone to a semiconductor substrate~~; and

polishing the semiconductor substrate at a pad pressure less than or equal to 21.7 kiloPascals, wherein ~~varying~~ increasing the weight ratio of the ~~thermoplastic polymer~~polyvinyl alcohol to the polyvinylpyrrolidone ~~controls~~ decreases the removal rate of the non-ferrous interconnect.

9. (Original) The method of Claim 8, wherein the polishing composition facilitates a removal rate of less than or equal to 150 Angstroms/minute for the low-k dielectric layer.

10. (Original) The method of Claim 8, wherein the polishing composition facilitates a removal rate of greater than or equal to 150 Angstroms/minute for the low-k dielectric layer.